

FDMS8662

N-Channel PowerTrench® MOSFET 30V, 49A, 2.0mΩ

Features

- Max $r_{DS(on)}$ = 2.0mΩ at $V_{GS} = 10V$, $I_D = 28A$
- Max $r_{DS(on)}$ = 3.0mΩ at $V_{GS} = 4.5V$, $I_D = 24A$
- Advanced Package and Silicon combination for low $r_{DS(on)}$ and high efficiency
- MSL1 robust package design
- RoHS Compliant

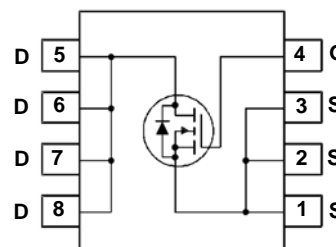
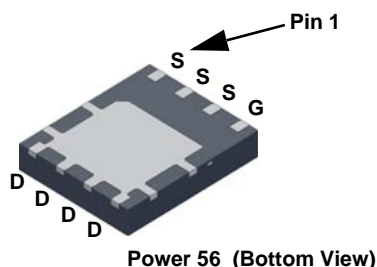


General Description

The FDMS8662 has been designed to minimize losses in power conversion application. Advancements in both silicon and package technologies have been combined to offer the lowest $r_{DS(on)}$ while maintaining excellent switching performance.

Applications

- Low Side for Synchronous Buck to Power Core Processor
- Secondary Side Synchronous Rectifier
- Low Side Switch in POL DC/DC Converter
- Oring FET/ Load Switch



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	30	V
V_{GS}	Gate to Source Voltage	± 20	V
I_D	Drain Current -Continuous (Package limited) $T_C = 25^\circ\text{C}$	49	A
	-Continuous (Silicon limited) $T_C = 25^\circ\text{C}$	159	
	-Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	28	
	-Pulsed	200	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	726	mJ
P_D	Power Dissipation $T_C = 25^\circ\text{C}$	83	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	2.5	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.5	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS8662	FDMS8662	Power 56	13"	12mm	3000units

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, referenced to 25°C		18		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{V}$, $V_{GS} = 0\text{V}$			1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$			± 100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu\text{A}$	1.0	1.7	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, referenced to 25°C		-7		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{V}$, $I_D = 28\text{A}$		1.6	2.0	m Ω
		$V_{GS} = 4.5\text{V}$, $I_D = 24\text{A}$		2.2	3.0	
		$V_{GS} = 10\text{V}$, $I_D = 28\text{A}$, $T_J = 125^\circ\text{C}$		2.2	3.0	
g_{FS}	Forward Transconductance	$V_{DD} = 10\text{V}$, $I_D = 28\text{A}$		207		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 15\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$		4825	6420	pF
C_{oss}	Output Capacitance			2365	3145	pF
C_{rss}	Reverse Transfer Capacitance			290	435	pF
R_g	Gate Resistance	$f = 1\text{MHz}$		1.1		Ω

Switching Characteristics

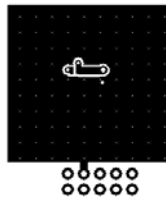
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\text{V}$, $I_D = 28\text{A}$, $V_{GS} = 10\text{V}$, $R_{GEN} = 6\Omega$		17	31	ns
t_r	Rise Time			10	20	ns
$t_{d(off)}$	Turn-Off Delay Time			45	72	ns
t_f	Fall Time			7	14	ns
Q_g	Total Gate Charge	$V_{GS} = 0\text{V}$ to 10V	$V_{DD} = 15\text{V}$, $I_D = 28\text{A}$	71	100	nC
Q_g	Total Gate Charge	$V_{GS} = 0\text{V}$ to 4.5V		33	47	nC
Q_{gs}	Gate to Source Charge			13		nC
Q_{gd}	Gate to Drain "Miller" Charge			9		nC

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}$, $I_S = 2.1\text{A}$ (Note 3)		0.7	1.2	V
		$V_{GS} = 0\text{V}$, $I_S = 28\text{A}$		0.8	1.2	V
t_{rr}	Reverse Recovery Time	$I_F = 28\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$		55	88	ns
Q_{rr}	Reverse Recovery Charge			42	68	nC

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1in^2 pad 2 oz copper pad on a $1.5 \times 1.5\text{in.}$ board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. $50^\circ\text{C}/\text{W}$ when mounted on a 1in^2 pad of 2 oz copper.



b. $125^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper.

2. Starting $T_J = 25^\circ\text{C}$, $L = 3\text{mH}$, $I_{AS} = 22\text{A}$, $V_{DD} = 30\text{V}$, $V_{GS} = 10\text{V}$.
3. Pulse Test: Pulse Width $< 300\mu\text{s}$, Duty cycle $< 2.0\%$.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

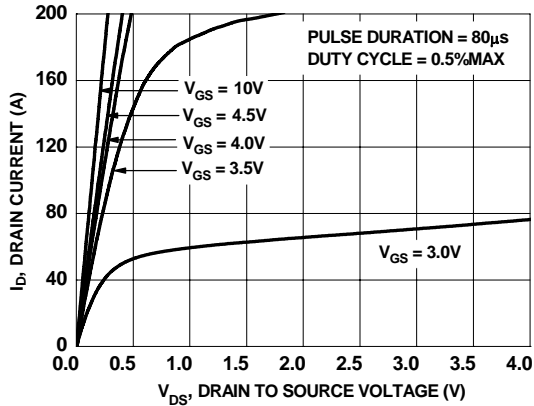


Figure 1. On-Region Characteristics

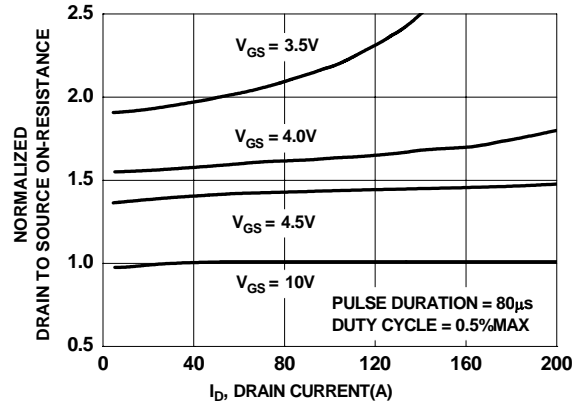


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

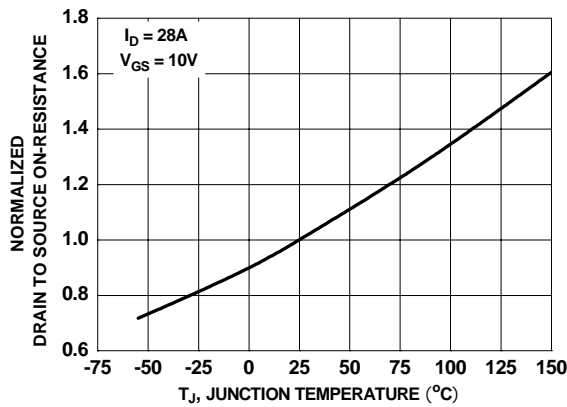


Figure 3. Normalized On-Resistance vs Junction Temperature

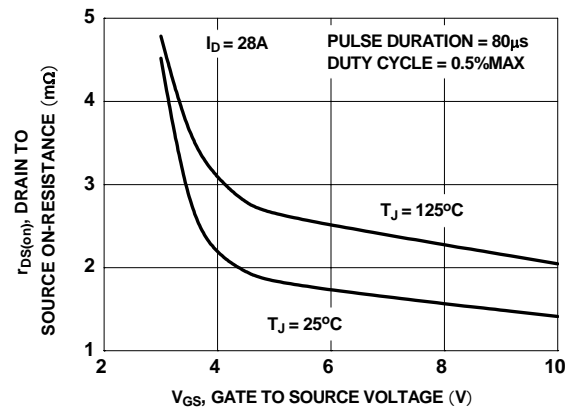


Figure 4. On-Resistance vs Gate to Source Voltage

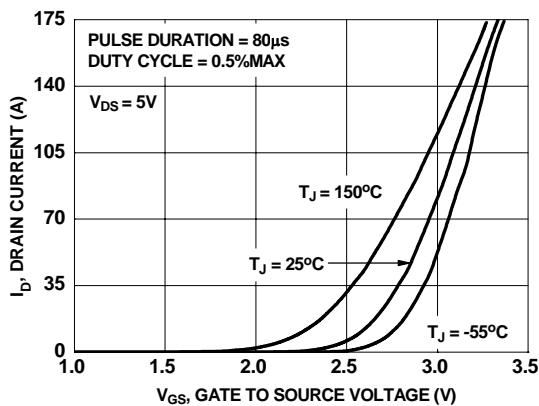


Figure 5. Transfer Characteristics

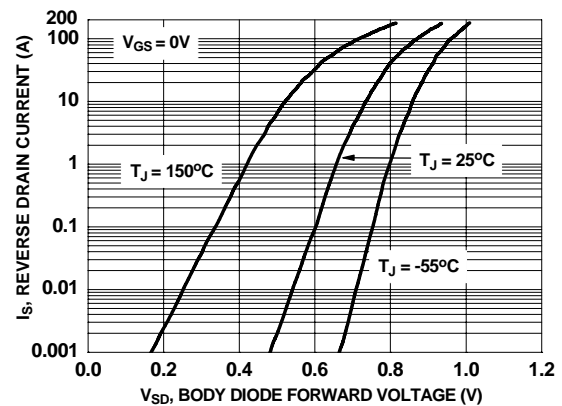


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

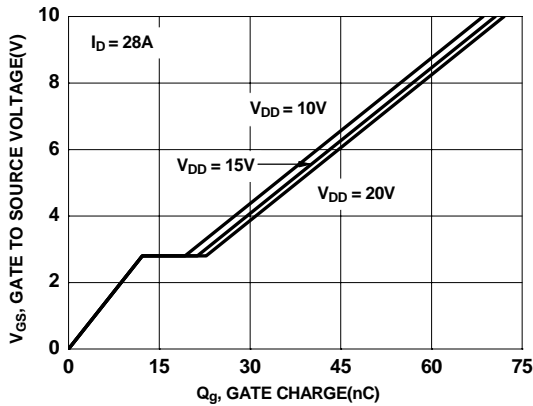


Figure 7. Gate Charge Characteristics

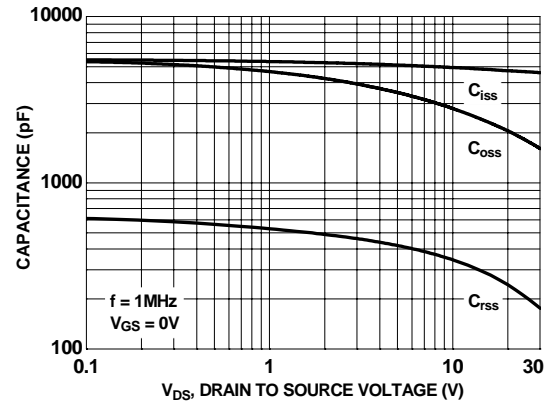


Figure 8. Capacitance vs Drain to Source Voltage

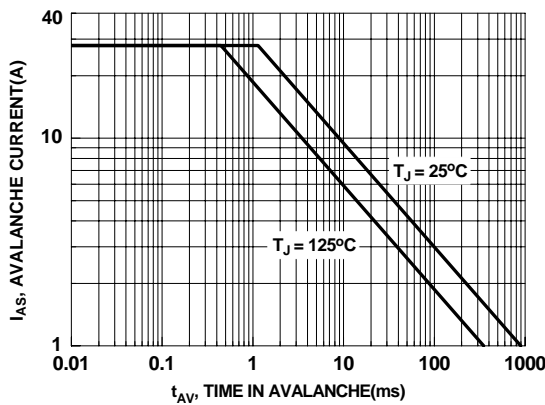


Figure 9. Unclamped Inductive Switching Capability

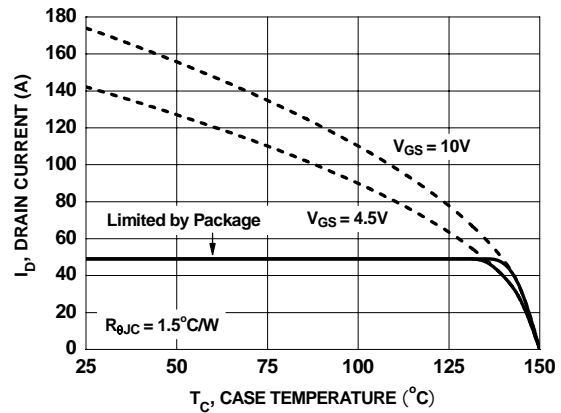


Figure 10. Maximum Continuous Drain Current vs Case Temperature

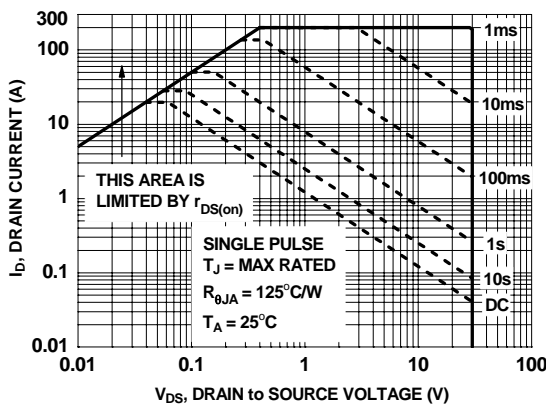


Figure 11. Forward Bias Safe Operating Area

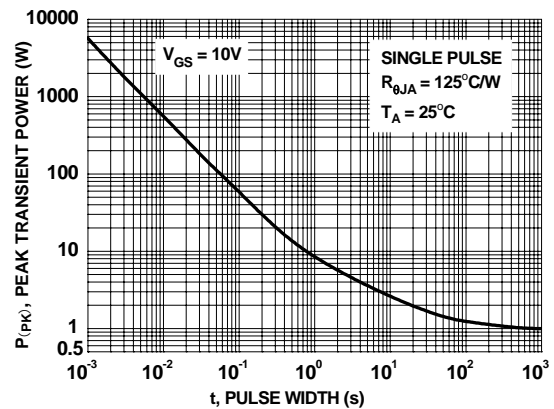
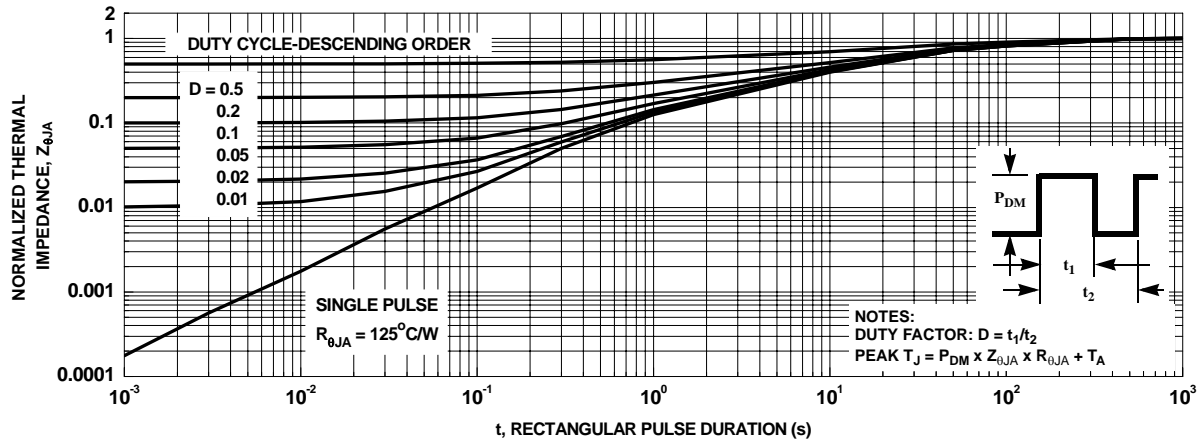
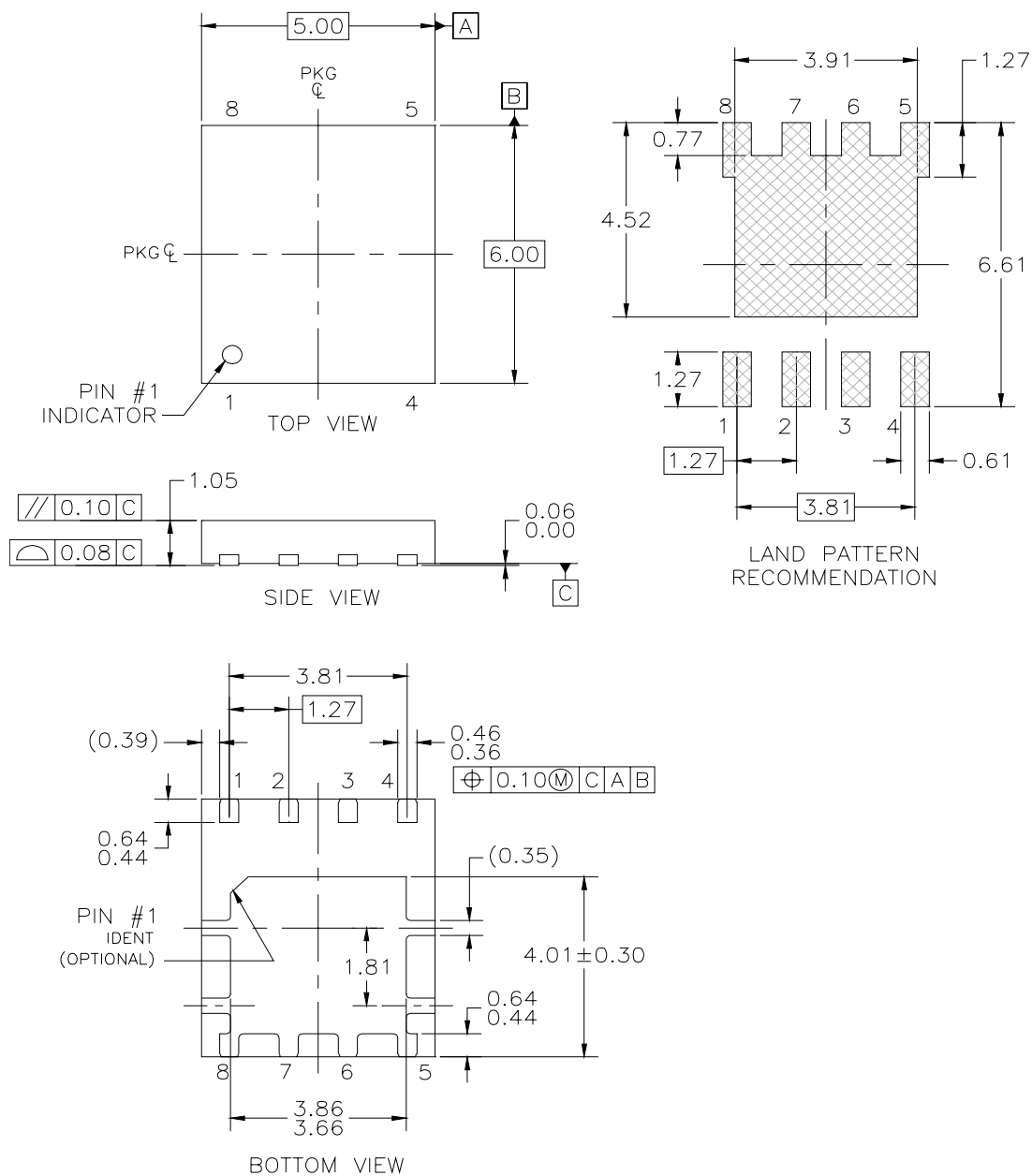


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted






- NOTES: UNLESS OTHERWISE SPECIFIED
- A) ALL DIMENSIONS ARE IN MILLIMETERS.
 - B) NO JEDEC REFERENCE AS OF FEBRUARY 2006
 - C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M 1994

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